

GENERAL PURPOSE APPLICATION.

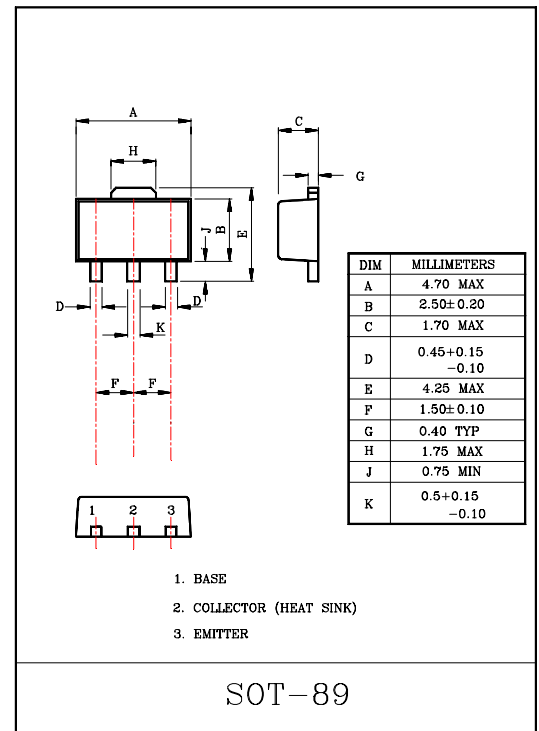
FEATURES

- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTA1662.

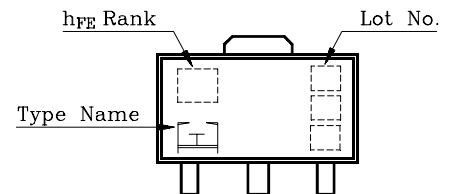
MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	400	mA
Base Current	I_B	80	mA
Collector Power Dissipation	P_C	500	mW
	P_{C^*}	1	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{slg}	-55~150	℃

P_{C^*} : KTC4374 mounted on ceramic substrate (250mm²×0.8t)



Marking



ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=80V, I_E=0$	—	—	100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	—	—	100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	80	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=2V, I_C=50mA$	70	—	240	
	$h_{FE(2)}$	$V_{CE}=2V, I_C=200mA$	50	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=200mA, I_B=20mA$	—	—	0.4	V
Base-Emitter Voltage	V_{BE}	$V_{BE}=2V, I_C=5mA$	0.55	—	0.8	V
Transition Frequency	f_T	$V_{CE}=10V, I_C=10mA$	—	100	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	—	10	—	pF

Note : h_{FE} Classification O:70~140, Y:120~240

